AO8818

Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

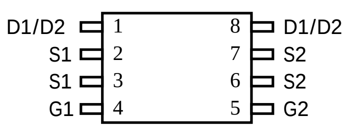
General Description

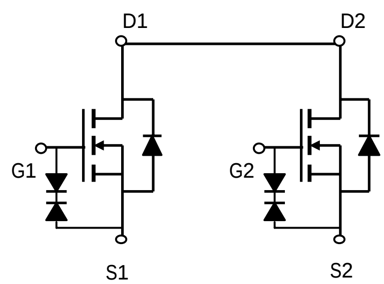
The AO8818 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration. *AO8818 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

V_{DS} (V) = 30V
I_D = 7A (V_{GS} = 10V)
$R_{DS(ON)}$ < 18mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 20mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 21mΩ (V_{GS} = 4V)
$R_{DS(ON)}$ < 24mΩ (V_{GS} = 3.1V)
$R_{DS(ON)}$ < 27mΩ (V_{GS} = 2.5V)
$R_{DS(ON)}$ < 58mΩ (V_{GS} = 1.8V)
ESD Rating: 1500V HBM

TSSOP-8
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current [A]	T_A=25°C	I_D	7	A
	T_A=70°C		5.5	
Pulsed Drain Current [B]		I_{DM}	30	
Power Dissipation [A]	T_A=25°C	P_D	1.5	W
	T_A=70°C		0.96	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	64	83	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		89	120	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	53	70	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±10V				10	µA
BV_{GSO}	Gate-Source Breakdown Voltage	V_{DS}=0V, I_G=±250uA		±12			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		0.6	0.94	1.5	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V		30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=7A		11.5	15	18	mΩ
			T_J=125°C	16	21	25	
		V_{GS}=4.5V, I_D=5A		13	17	20	mΩ
		V_{GS}=4V, I_D=5A		13.5	17.5	21	
		V_{GS}=3.1V, I_D=5A		15	19.5	24	
		V_{GS}=2.5V, I_D=4A		17	22	27	mΩ
		V_{GS}=1.8V, I_D=3A		35	45	58	
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=7A			45		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.74	1	V
I_S	Maximum Body-Diode Continuous Current					2.5	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz			880	1060	pF
C_{oss}	Output Capacitance				130		pF
C_{rss}	Reverse Transfer Capacitance				90		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			1.3	2	Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=7A			11.6	14	nC
Q_{gs}	Gate Source Charge				1.9		nC
Q_{gd}	Gate Drain Charge				4.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=15V, R_L=2.2Ω, R_{GEN}=3Ω			8.7		ns
t_r	Turn-On Rise Time				13.7		ns
$t_{D(off)}$	Turn-Off DelayTime				36		ns
t_f	Turn-Off Fall Time				11		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=7A, dI/dt=100A/µs			16	20	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=7A, dI/dt=100A/µs			7.7		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using <300 µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 2: Feb 2008

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

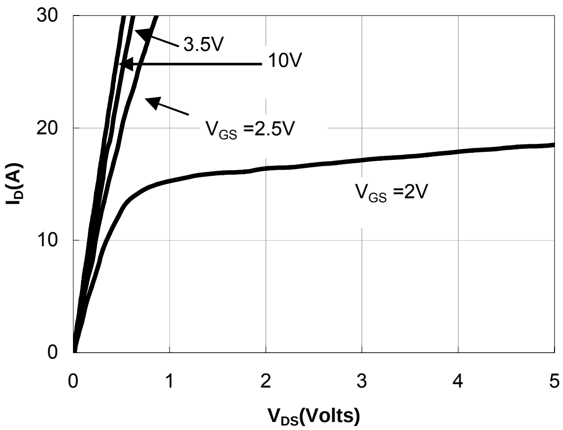


Figure 1: On-Regions Characteristics

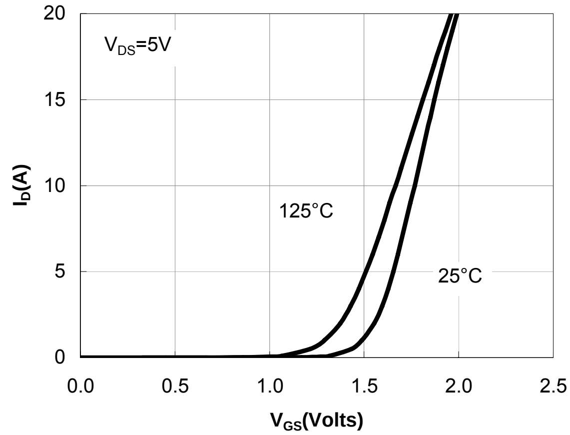


Figure 2: Transfer Characteristics

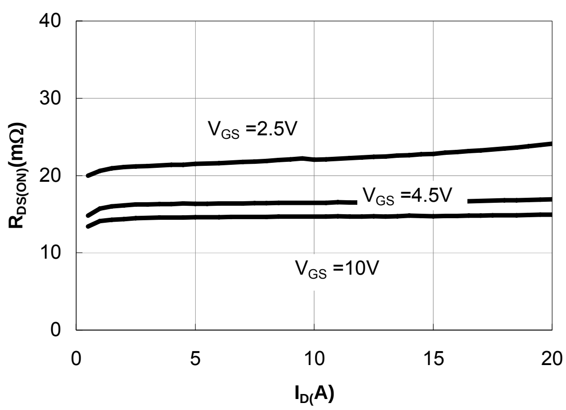


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

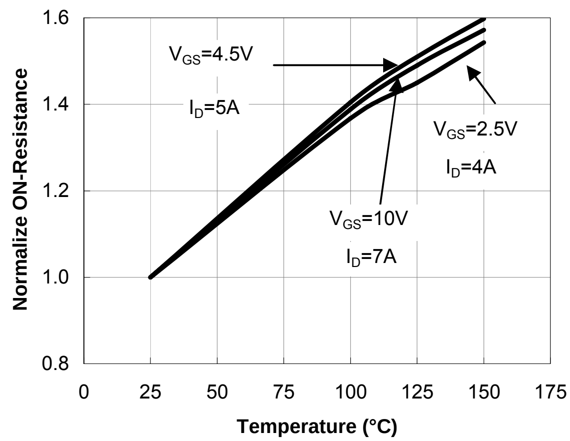


Figure 4: On-Resistance vs. Junction Temperature

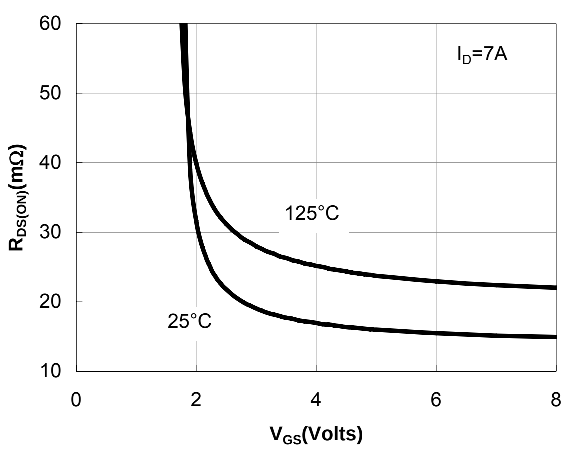


Figure 5: On-Resistance vs. Gate-Source Voltage

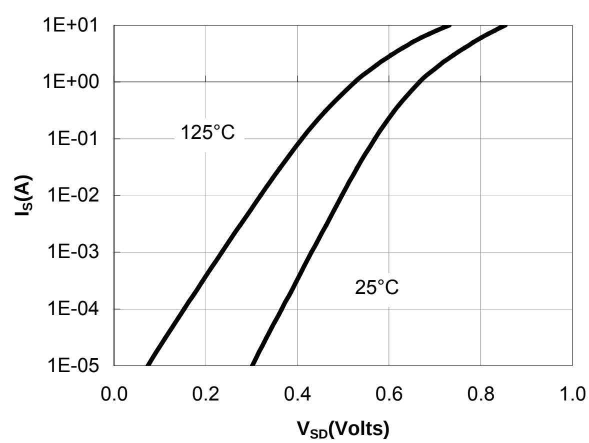


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

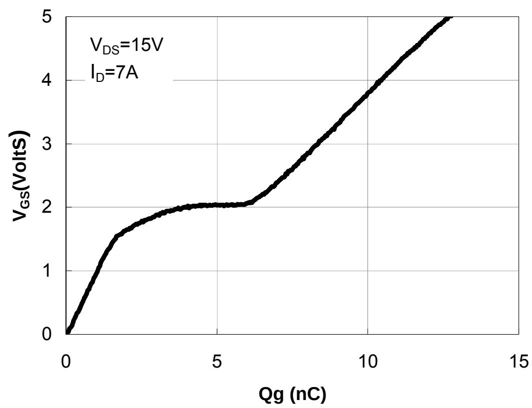


Figure 7: Gate-Charge Characteristics

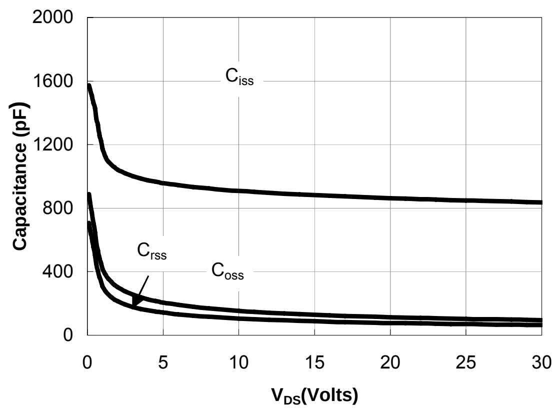


Figure 8: Capacitance Characteristics

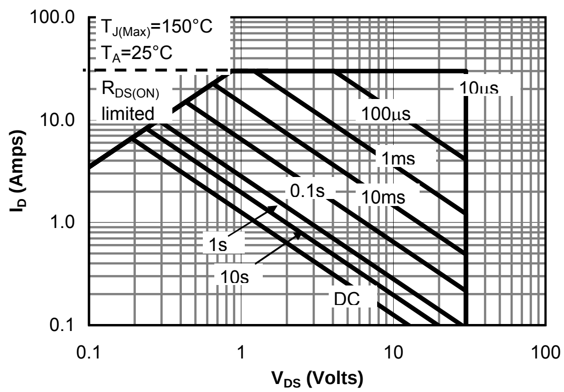


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

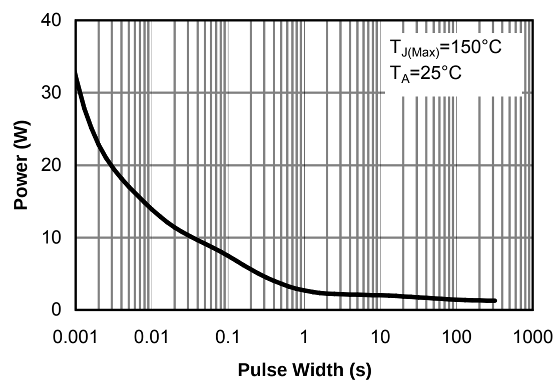


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

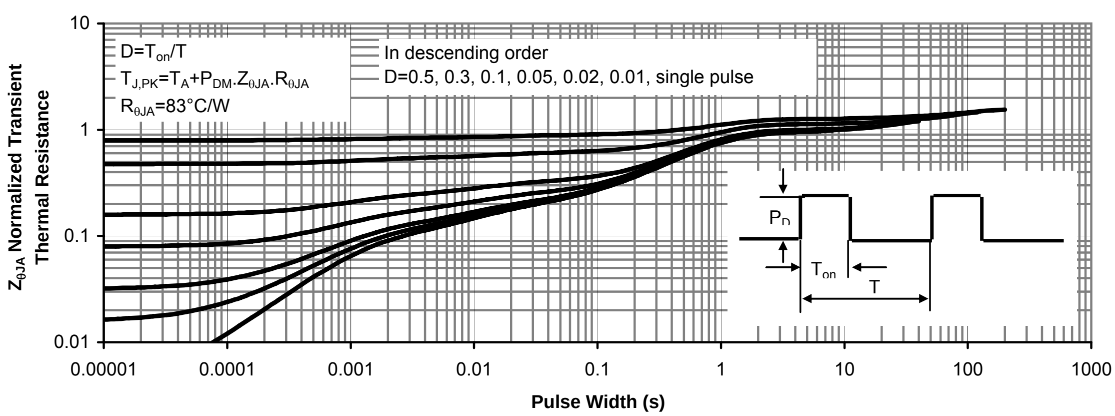


Figure 11: Normalized Maximum Transient Thermal Impedance